BAV70WT1

Preferred Device

Dual Switching Diode Common Cathode

Features

• Pb-Free Package is Available

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Reverse Voltage	V _R	70	V
Forward Current	IF	200	mA
Peak Forward Surge Current	I _{FM(surge)}	500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

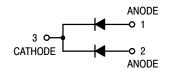
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	200	mW mW/°C
Thermal Resistance, Junction–to–Ambient	R _θ JA	625	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



ON Semiconductor®

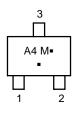
http://onsemi.com



MARKING DIAGRAM



SOT-323 CASE 419 STYLE 5



A4 = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BAV70WT1	SOT-323	3000/Tape & Reel
BAV70WT1G	SOT-323 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage (I _(BR) = 100 μA)	V _(BR)	70	-	V
Reverse Voltage Leakage Current (Note 3) (V _R = 70 V) (V _R = 50 V)	I _R	- -	5.0 100	μA nA
Forward Voltage (I _F = 1.0 mA) (I _F = 10 mA) (I _F = 50 mA) (I _F = 150 mA)	V _F	- - - -	715 855 1000 1250	mV
Diode Capacitance (V _R = 0 V, f = 1.0 MHz)	C _D	-	1.5	pF
Reverse Recovery Time (I _F = I _R = 10 mA, R _L = 100 Ω , I _{R(REC)} = 1.0 mA) (Figure 1)	t _{rr}	-	6.0	ns
Forward Recovery Voltage ($I_F = 10 \text{ mA}, t_f = 20 \text{ ns}$) (Figure 2)	V _{RF}	-	1.75	V

^{3.} For each individual diode while the second diode is unbiased.

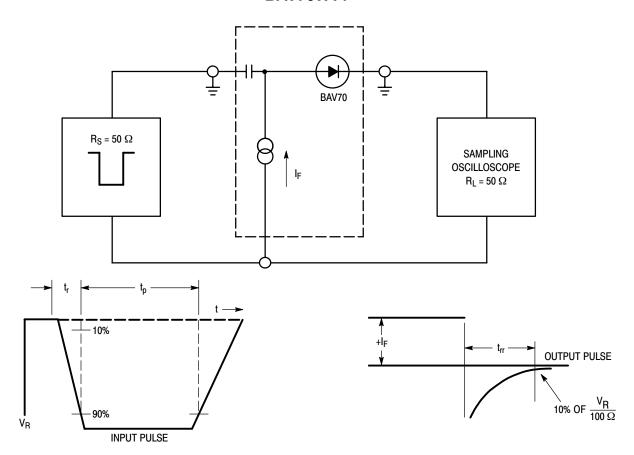
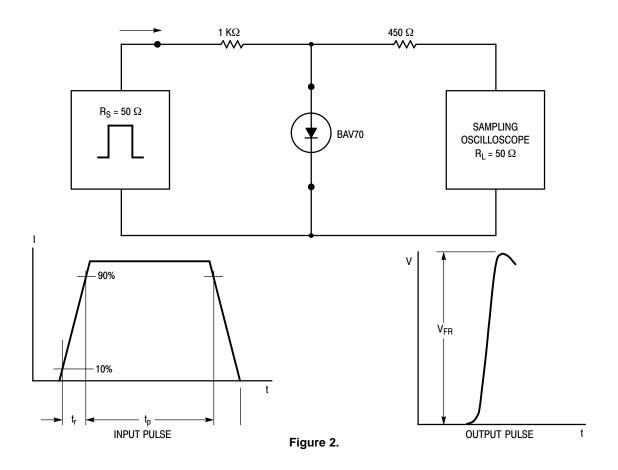


Figure 1. Recovery Time Equivalent Test Circuit



BAV70WT1

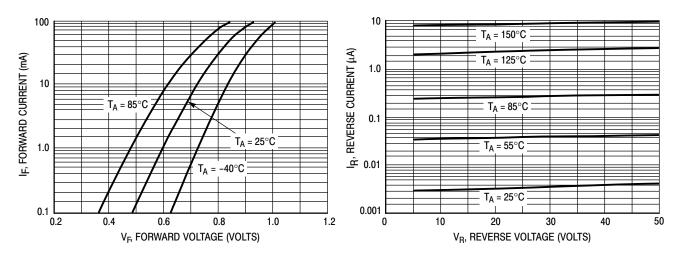


Figure 3. Forward Voltage

Figure 4. Leakage Current

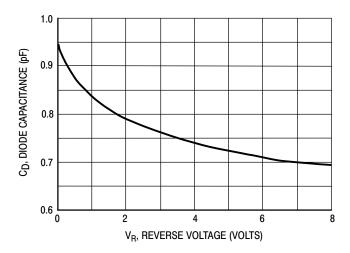
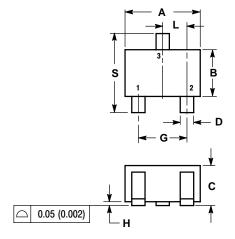


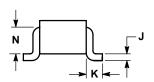
Figure 5. Capacitance

BAV70WT1

PACKAGE DIMENSIONS

SOT-323 (SC-70) CASE 419-04 ISSUE L





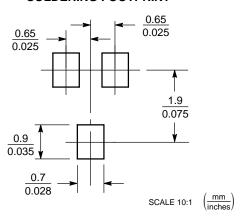
IOTES.

- DIMENSIONING AND TOLERANCING PER ANSI
 VIA EM 1000
- 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.032	0.040	0.80	1.00	
D	0.012	0.016	0.30	0.40	
G	0.047	0.055	1.20	1.40	
Н	0.000	0.004	0.00	0.10	
J	0.004	0.010	0.10	0.25	
K	0.017 REF		0.425 REF		
L	0.026 BSC		0.650	0.650 BSC	
N	0.028 REF		0.700 REF		
S	0.079	0.095	2.00	2.40	

STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and was registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights or the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2–9–1 Kamimeguro, Meguro–ku, Tokyo, Japan 153–0051 Phone: 81–3–5773–3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.